

HD74ALVC162835

18-bit Universal Bus Driver with 3-state Outputs

REJ03D0055-0700Z (Previous ADE-205-201E (Z)) Rev.7.00 Oct.02.2003

Description

The HD74ALVC162835 is an 18-bit universal bus driver designed for 2.3 V to 3.6 V V_{CC} operation.

Data flow from A to Y is controlled by the output enable (\overline{OE}) . The device operates in the transparent mode when the latch enable (LE) is high. When LE is low, the A data is latched if the clock (CLK) input is held at a high or low logic level. If the LE is low, the A data is stored in the latch/flip flop on the low to high transition of CLK. When \overline{OE} is high, the outputs are in the high impedance state.

To ensure the high impedance state during power up or power down, \overline{OE} should be tied to V_{CC} through a pullup register; the minimum value of the register is determined by the current sinking capability of the driver.

All outputs, which are designed to sink up to 12 mA, include 26 Ω resistors to reduce overshoot and undershoot.

Features

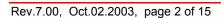
- Meets "PC SDRAM registered DIMM design support document, Rev. 1.2"
- $V_{CC} = 2.3 \text{ V to } 3.6 \text{ V}$
- Typical V_{OL} ground bounce $< 0.8 \text{ V } (@V_{CC} = 3.3 \text{ V}, \text{Ta} = 25^{\circ}\text{C})$
- Typical V_{OH} undershoot > 2.0 V (@ V_{CC} = 3.3 V, Ta = 25°C)
- High output current $\pm 12 \text{ mA}$ (@V_{CC} = 3.0 V)
- All outputs have equivalent 26 Ω series resistors, so no external resistors are required

Function Table

Inputs		Output Y		
ŌĒ	LE	CLK	Α	_
Н	Х	Х	Х	Z
L	Н	Х	L	L
L	Н	Х	Н	Н
L	L	↑	L	L
L	L	↑	Н	Н
L	L	L or H	X	Y ₀ *1

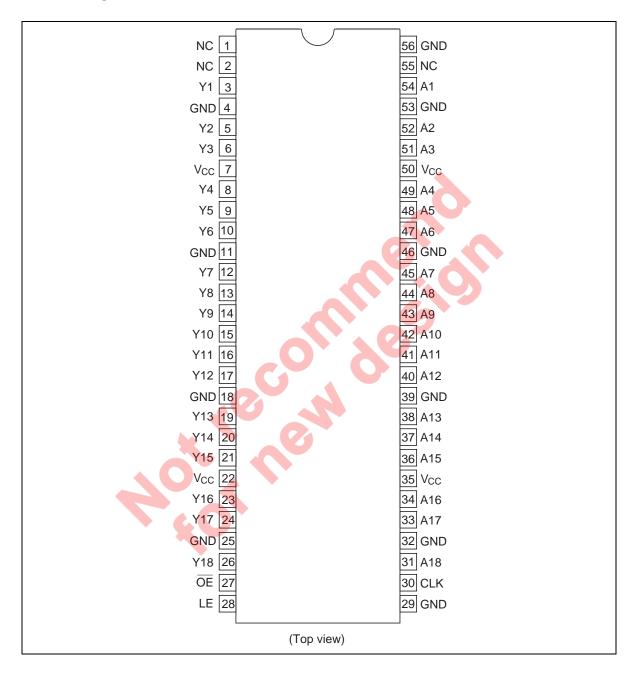
H: High level
L: Low level
X: Immaterial
Z: High impedance
↑: Low to high transition

Note: 1. Output level before the indicated steady-state input conditions were established.





Pin Arrangement



Absolute Maximum Ratings

Item	Symbol	Ratings	Unit	Conditions
Supply voltage range	V _{CC}	-0.5 to 4.6	V	
Input voltage range *1	Vı	-0.5 to 4.6	V	
Output voltage range *1, 2	Vo	-0.5 to V _{CC} +0.5	V	
Input clamp current	I _{IK}	– 50	mA	V _I < 0
Output clamp current	I _{OK}	±50	mA	$V_O < 0$ or $V_O > V_{CC}$
Continuous output current	Io	±50	mA	$V_{\rm O}$ = 0 to $V_{\rm CC}$
V _{CC} , GND current / pin	I _{CC} or I _{GND}	±100	mA	
Maximum power dissipation at Ta = 55°C (in still air) *3	P _T	1	W	TSSOP
Storage temperature range	Tstg	-65 to 150	°C	

Notes: Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating condition" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

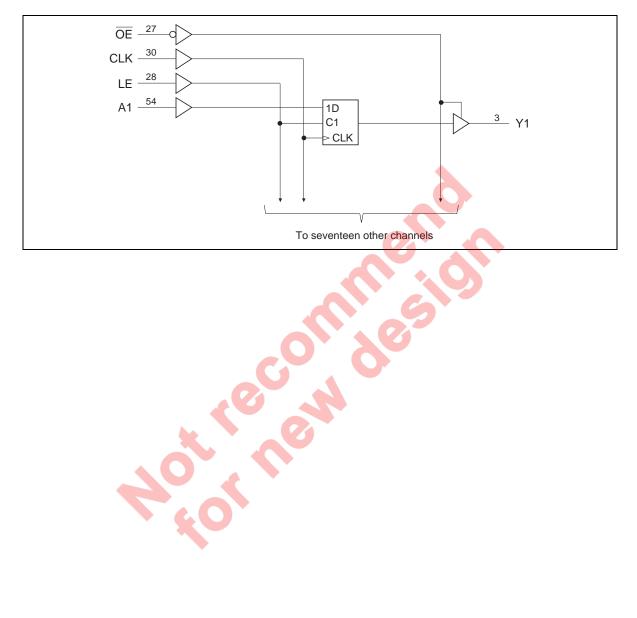
- 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp current ratings are observed.
- 2. The input and output positive-voltage ratings may be exceeded up to 4.6 V if the input and output clamp-current ratings are observed.
- 3. The maximum power dissipation is calculated using a junction temperature of 150°C and board trace length of 750 mils.

Recommended Operating Conditions

Item	Symbol	Min	Max	Unit	Conditions
Supply voltage	V _{CC}	2.3	3.6	V	
Input voltage	Vi	0	V _{CC}	V	
Output voltage	Vo	0	Vcc	V	
High-level output current	I _{OH}	_	- 6	mA	V _{CC} = 2.3 V
		_	-8	_	V _{CC} = 2.7 V
		_	-12	_	V _{CC} = 3.0 V
Low-level output current	I _{OL}	_	6	mA	V _{CC} = 2.3 V
		_	8	_	V _{CC} = 2.7 V
		_	12	_	V _{CC} = 3.0 V
Input transition rise or fall rate	Δt/Δν	0	10	ns/V	
Operating free-air temperature	Та	-4 0	85	°C	

Note: Unused or floating control pins must be held high or low.

Logic Diagram



Electrical Characteristics

 $Ta = -40 \text{ to } 85^{\circ}C$

			14 - T	0 10 00 0		
Item	Symbol	V _{CC} (V)	Min	Max	Unit	Test Conditions
Input voltage	V _{IH}	2.3 to 2.7	1.7	_	V	
		2.7 to 3.6	2.0	_	-	
	V _{IL}	2.3 to 2.7	_	0.7	V	
		2.7 to 3.6	_	0.8	_	
Output voltage	V _{OH}	2.3 to 3.6	V _{CC} -0.2	_	V	I _{OH} = -100 μA
		2.3	1.9	_	-	I _{OH} = -4 mA, V _{IH} = 1.7 V
		2.3	1.7	_	_	$I_{OH} = -6 \text{ mA}, V_{IH} = 1.7 \text{ V}$
		3.0	2.4	_	_	I _{OH} = -6 mA, V _{IH} = 2.0 V
		2.7	2.0	_		I _{OH} = -8 mA, V _{IH} = 2.0 V
		3.0	2.0	_		$I_{OH} = -12 \text{ mA}, V_{IH} = 2.0 \text{ V}$
	V _{OL}	2.3 to 3.6	_	0.2	V	I _{OL} = 100 μA
		2.3	_	0.4		I _{OL} = 4 mA, V _{IL} = 0.7 V
		2.3	- 4	0.55	6	I _{OL} = 6 mA, V _{IL} = 0.7 V
		3.0	-	0.55		I _{OL} = 6 mA, V _{IL} = 0.8 V
		2.7	(-)	0.6		I _{OL} = 8 mA, V _{IL} = 0.8 V
		3.0		8.0		I _{OL} = 12 mA, V _{IL} = 0.8 V
Input current	I _{IN}	3.6	- 3	±5.0	μΑ	V _{IN} = V _{CC} or GND
Off state output current	loz	3.6	-	±10	μΑ	V _{OUT} = V _{CC} or GND
Quiescent supply current	Icc	3.6	(3)	40	μΑ	$V_{IN} = V_{CC}$ or GND
	ΔI_{CC}	3.0 to 3.6		750	μA	One input at (V _{CC} –0.6)V, other inputs at V _{CC} or GND

Switching Characteristics

 $(Ta = -40 \text{ to } 85^{\circ}C)$

Item	Symbol	V _{CC} (V)	Min	Тур	Max	Unit	From (Input)	To (Output)
Maximum clock	f _{max}	2.5±0.2	150	_	_	MHz		
frequency		2.7	150	_	_	_		
		3.3±0.3	150	_	_	_		
Propagation delay time	t _{PLH}	2.5±0.2	1.0	_	5.0	ns	Α	Υ
	t_{PHL}	2.7	_	_	5.0	_		
		3.3±0.3	1.0	_	4.2	_		
		2.5±0.2	1.3	_	5.9		LE	Υ
		2.7	_	_	5.8			
		3.3±0.3	1.3	_	5.1			
		2.5±0.2	1.4	_	6.3		CLK	Υ
		2.7	_	_	6.1	_ (
		3.3±0.3	1.4	_ <	5.4			
Output enable time	t _{zH}	2.5±0.2	1.4		6.3	ns	ŌĒ	Υ
	t_{ZL}	2.7			6.5			
		3.3±0.3	1.1		5.5	_		
Output disable time	t _{HZ}	2.5±0.2	1.0	_ \	4.7	ns	ŌĒ	Υ
	t_{LZ}	2.7		-	4.9	_		
		3.3±0.3	1.3	77	4.5	_		
Input capacitance	CIN	3.3	3.0	4.5	7.0	pF	Control inputs	1
		3.3	3.0	6.0	9.0	_	Data inputs	
Output capacitance	Co	3.3	3.0	7.0	9.0	pF	Y ports	

HD74ALVCH162835

Switching Characteristics (cont.)

 $(Ta = -40 \text{ to } 85^{\circ}C)$

Item	Symbol	V _{CC} (V)	Min	Тур	Max	Unit	From (Input)
Setup time	t _{su}	2.5±0.2	2.2	_	_	ns	Data before CLK↑
		2.7	2.1	_	_	_	
		3.3±0.3	1.7	_	_	_	
		2.5±0.2	1.9	_	_	_	Data before LE ↑
		2.7	1.6	_	_	_	CLK "H"
		3.3±0.3	1.5	_	_	_	
		2.5±0.2	1.3	_	_		Data before LE↑
		2.7	1.1	_	_		CLK "L"
		3.3±0.3	1.0	_			
Hold time	t _h	2.5±0.2	0.6	_	+13	ns	Data after CLK↑
		2.7	0.6		7	(
		3.3±0.3	0.7	- (-		
		2.5±0.2	1.4	-			Data after LE ↑
		2.7	1.7	- /	1		CLK "H" or "L"
		3.3±0.3	1.4	_	7	_	
Pulse width	t _w	2.5±0.2	3.3	_ \	<u></u>	ns	LE "L"
		2.7	3.3	1	_	_	
		3.3±0.3	3.3	7	_	_	
		2.5±0.2	3.3	_	_	_	CLK "H" or "L"
		2.7	3.3	_	_	_	
		3.3±0.3	3.3	_	_	_	

Switching Characteristics (cont.)

 $(Ta = 0 \text{ to } 85^{\circ}C)$

Item		Symbol	V _{CC} (V)	Min	Тур	Max	Unit	FROM (Input)	TO (Output)
Propagation	C _L =0pF *1	t _{PLH} , t _{PHL}	3.3±0.165	0.9	_	2.0	ns	Α	Υ
delay time	C _L =50pF	_	3.3±0.165	1.0	_	4.5			
	C _L =0pF *1	_	3.3±0.165	1.4	_	2.9		CLK	Υ
	C _L =50pF	_	3.3±0.165	1.9	_	4.5	_		
	C _L =50pF	t _{SSO} *1, 2	3.3±0.165	1.9	_	4.8	_	CLK, A	Υ
Output rise / fall time	C _L =50pF	t _{TLH} , t _{THL}	3.3±0.165	1.0	_	2.5	volts/ ns	>	Y

Notes: 1. This parameter is characterized but not tested.

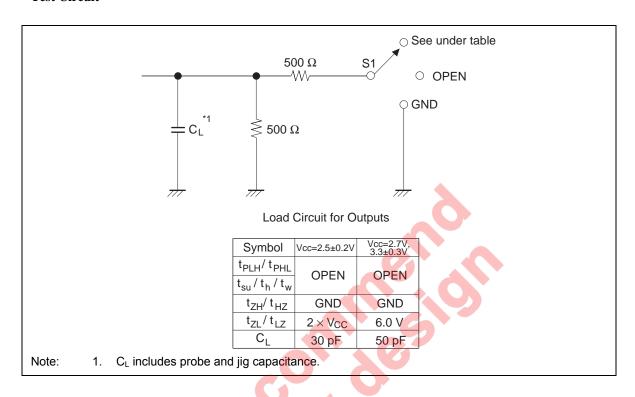
2. t_{SSO} : Simultaneous switching output time.

Operating Characteristics

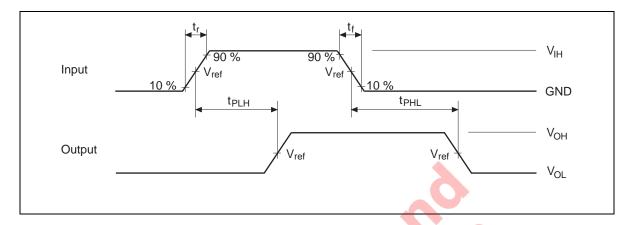
 $(Ta = 25 \, ^{\circ}C)$

Item	Syr	mbol	V _{CC} = 2.5	±0.2 V	$V_{CC} = 3.3 \pm 0.3 \text{ V}$	Unit	Test Conditions
		7	Тур		Тур		
Power dissipation	Outputs enable C _{pd}		22.0		24.5	pF	C _L = 0, f = 10 MHz
capacitance	Outputs disable		5.0		6.0	_	

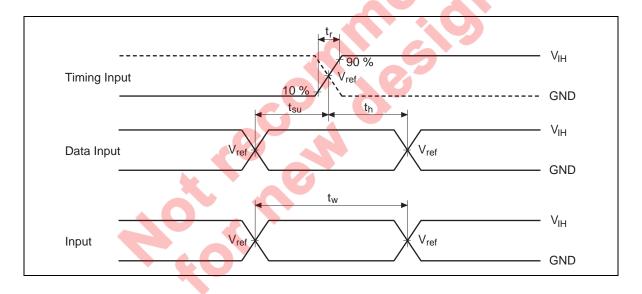
Test Circuit



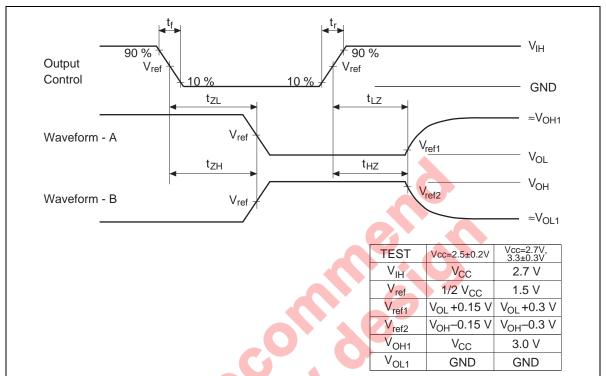
Waveforms - 1



Wave forms -2



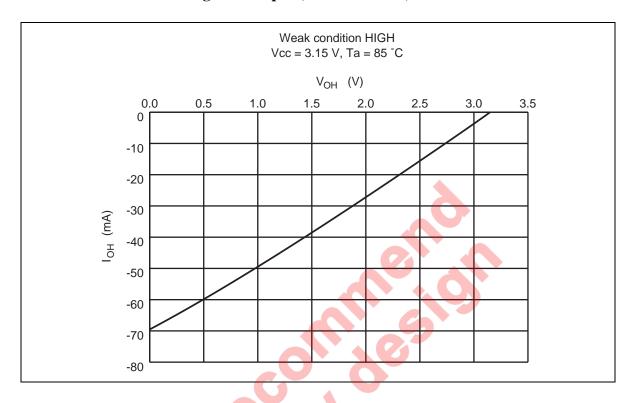
Wave forms - 3

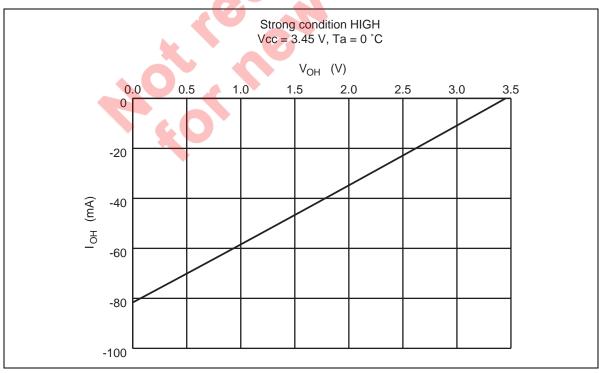


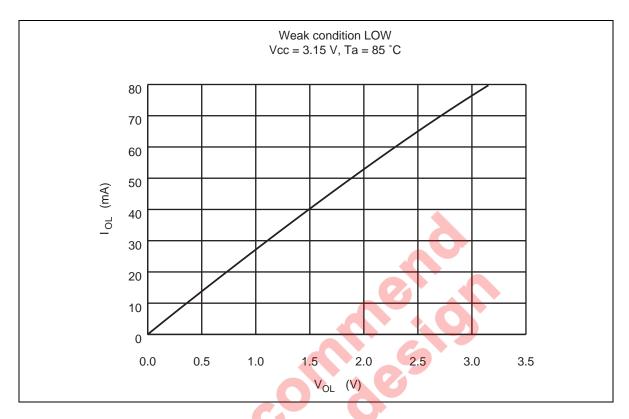
Notes:

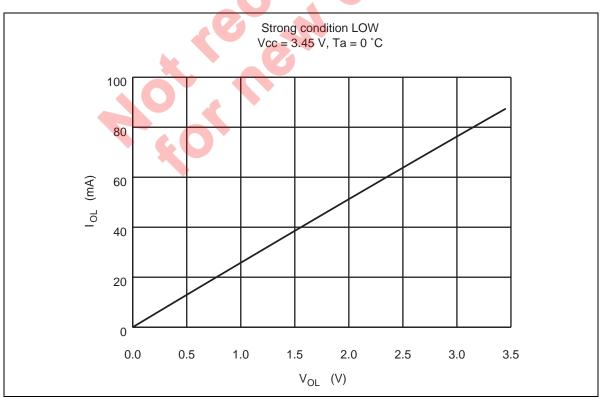
- 1. All input pulses are supplied by generators having the following characteristics : PRR \leq 10 MHz, Zo = 50 Ω , tr \leq 2.0 ns, tf \leq 2.0 ns. (V_{CC} = 2.5±0.2 V) PRR \leq 10 MHz, Zo = 50 Ω , tr \leq 2.5 ns, tf \leq 2.5 ns. (V_{CC} = 2.7 V, 3.3±0.3 V)
- 2. Waveform A is for an output with internal conditions such that the output is low except when disabled by the output control.
- 3. Waveform B is for an output with internal conditions such that the output is high except when disabled by the output control.
- 4. The output are measured one at a time with one transition per measurement.

IV Characteristics for Register Output (Measured value)

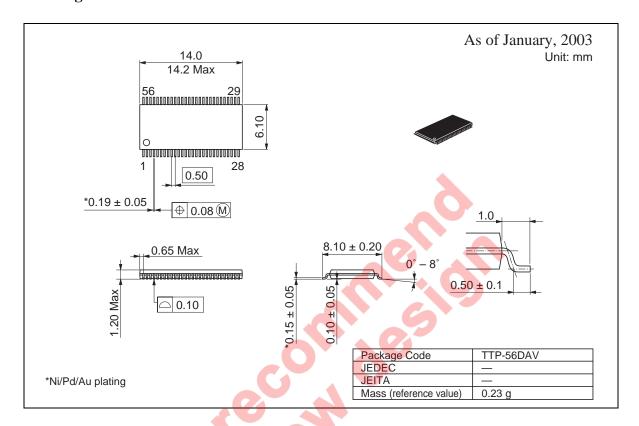








Package Dimensions



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